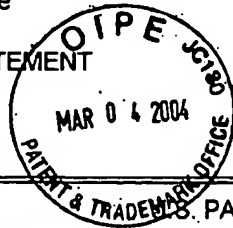


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10/646,457

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M.Feng, N. Holonyak, & W. Hafez

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J. H. Chen

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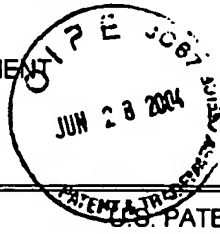
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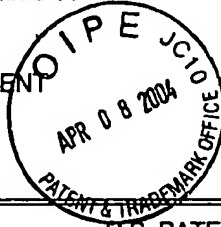
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